

PDFN 3×3A-8L P MOS

P-Channel Enhancement Mode Field Effect Transistor in a PDFN3×3A-8L Plastic Package.

$V_{DS} (V) = -60V$   $I_D = -23A (V_{GS} = \pm 20V)$

$R_{DS(ON)} @ -10V$  40m (Typ.36m )

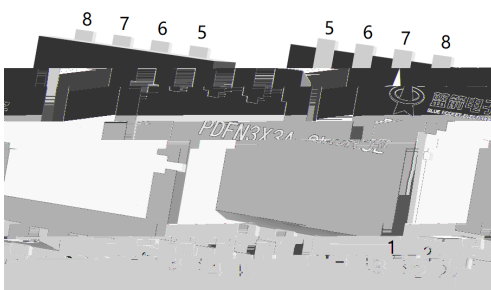
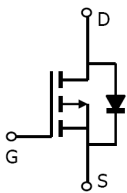
$R_{DS(ON)} @ -4.5V$  50m (Typ.44m )

AEC-Q101  
 HF Product.

Qualified to AEC-Q101 Standards for High Reliability,

/

Notebook AC-in load switch, Battery protection charge/discharge, Meet the stringent requirements of automotive applications.



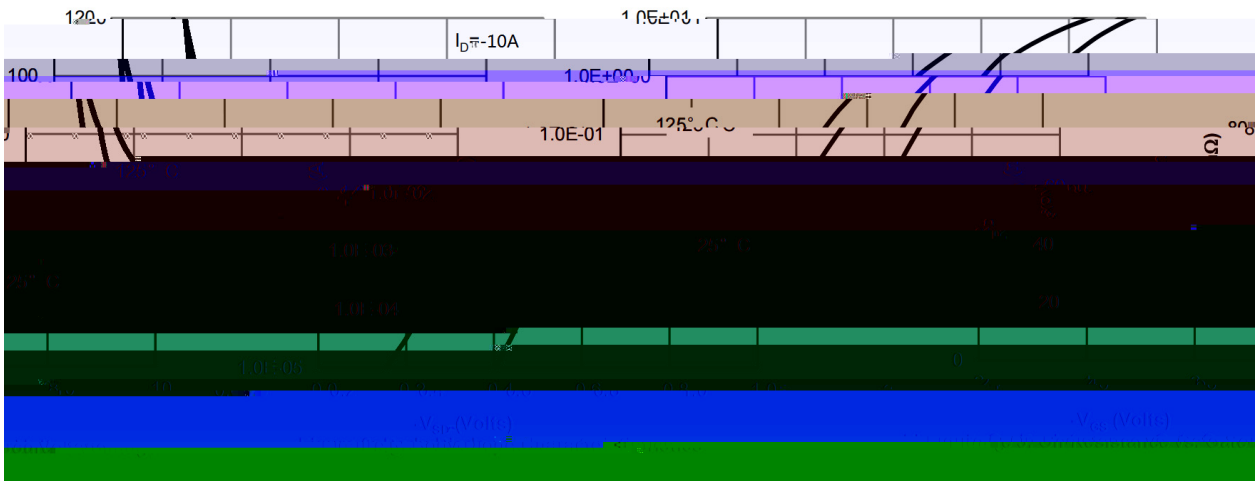
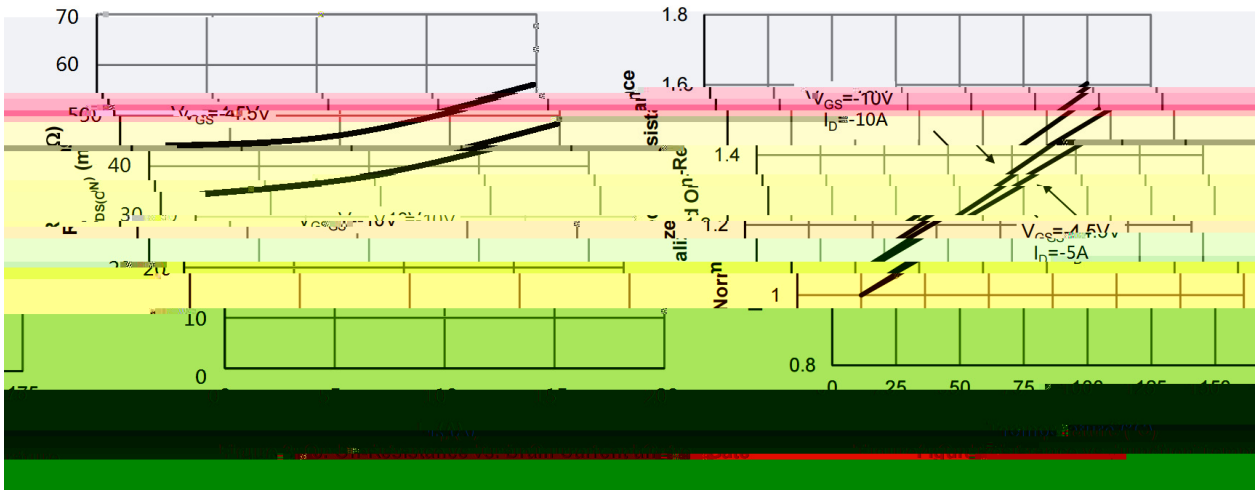
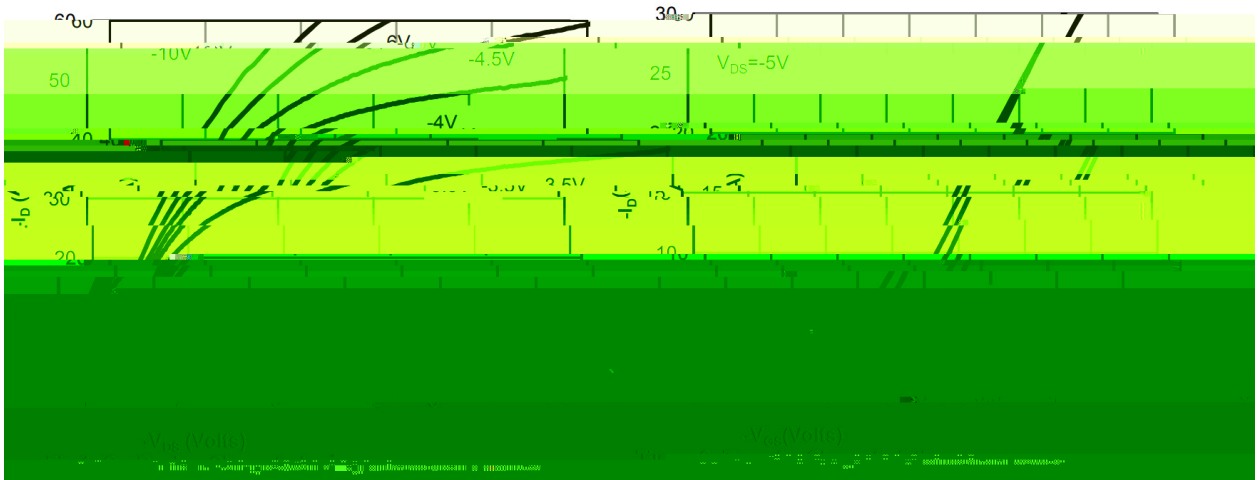
出脚	定义
Pin1	S
Pin2	S
3	S
4	S
5	S
6	S
7	S
8	S

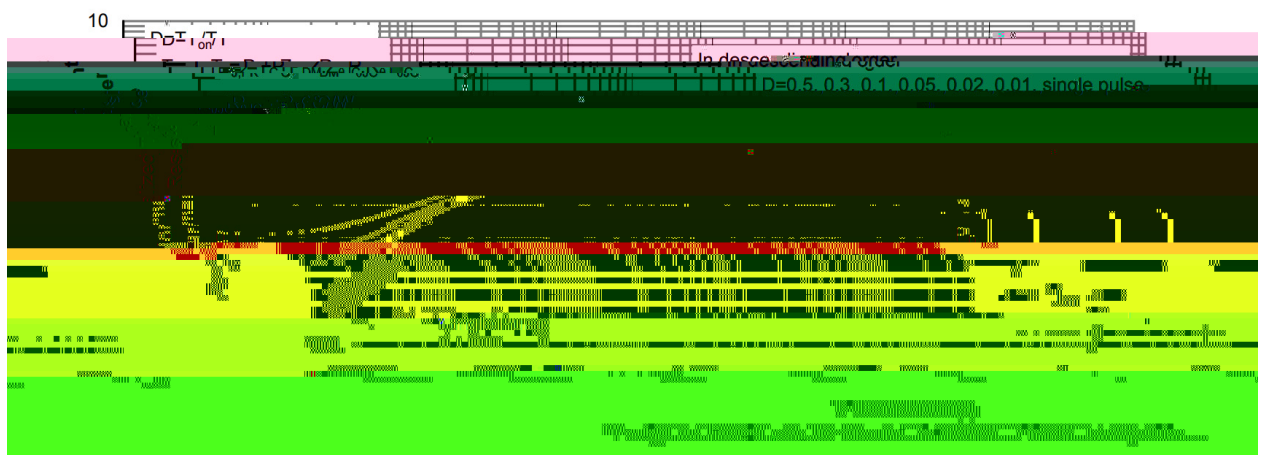
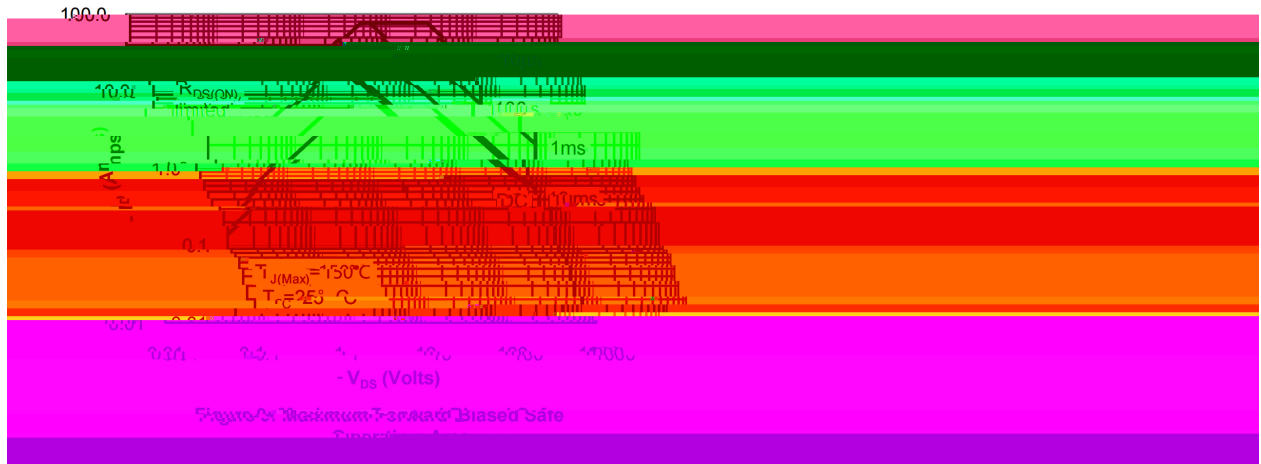
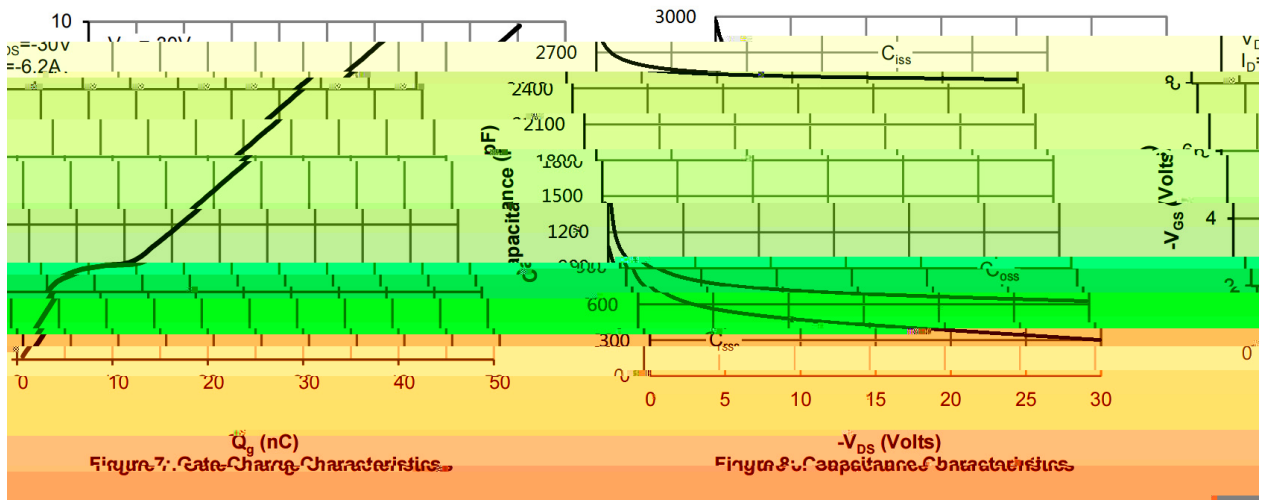
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DSS}$	-60	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Continuous Drain Current	$I_D (T_c=25^\circ C)$	-23	A
Pulsed Drain Current	$I_{DM}$	-73	A
Avalanche Current	$I_{AS}$	17.5	A
Avalanche energy $L=0.5mH$	$E_{AS}$	320	mJ
Power Dissipation for Single Operation	$P_D (T_c=25^\circ C)$	35	W

Maximum Junction Temperature  $T_{jmax}$  155.62 1.6921 0 TD0 Tc@1073j/T002 Tc.0025 Tw( T)Tm-.4720e480043 T604 Tm0 T

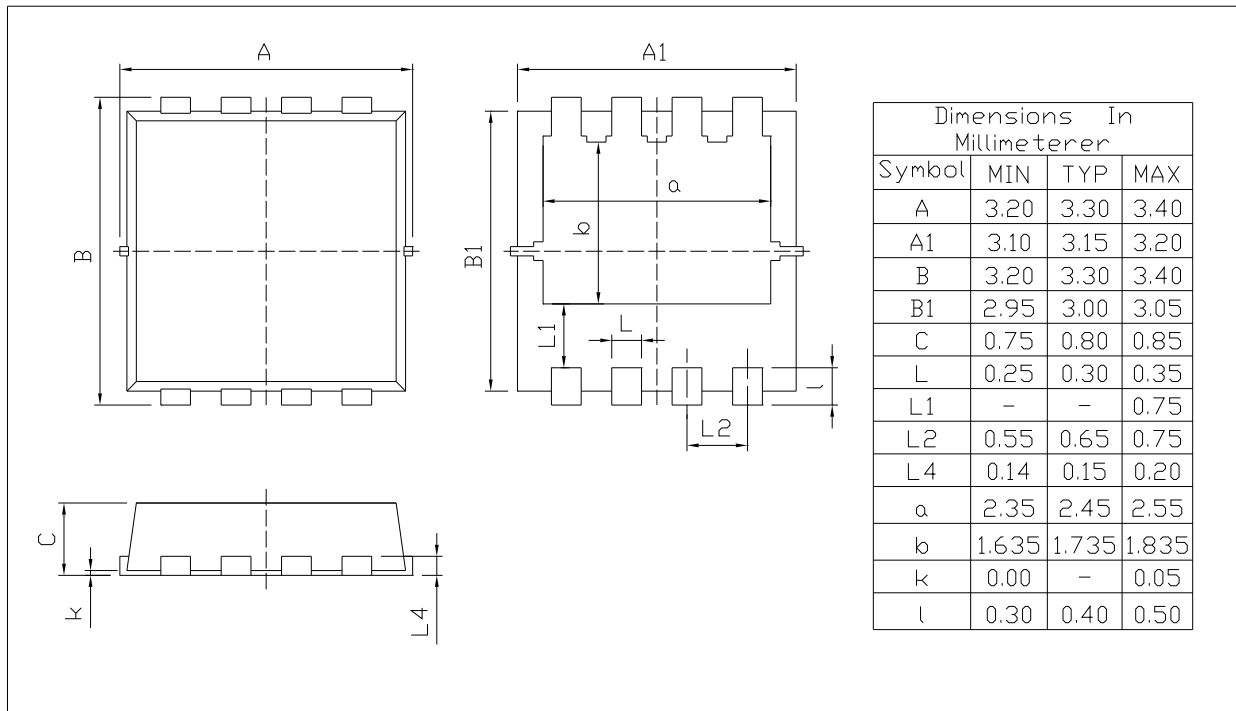
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=-10V$ $V_{DS}=-30V$ $I_D=-6.2A$		46.5		nC
Total Gate Charge	$Q_{g(4.5V)}$			22.7		
Gate-Source Charge	$Q_{gs}$			9.1		
Gate-Drain Charge	$Q_{gd}$			9.2		
Turn-on Delay Time	$t_{d(ON)}$	$V_{GS}=-10V$ $V_{DS}=-30V$ $R_L=4.7$ $R_{GEN}=3$		9.8		ns
Turn-on Rise Time	$t_r$			6.1		
Turn-off Delay Time	$t_{d(OFF)}$			44		
Turn-off Fall Time	$t_f$			12.7		





## PDFN3X3A-8L

Unit:mm



Rev.00 202011



BR

Q

400P06

\*\*\*\*

Note:

BR: Company Code

Q: Automobile halogen-free product Code

400P06: Product Type Code

\*\*\*\*: Lot No. Code, code change with Lot No

